# 2SA1810

## Silicon PNP Epitaxial

# **HITACHI**

### **Application**

High frequency amplifier

#### **Features**

- Excellent high frequency characteristics
   f<sub>T</sub> = 300 MHz typ
- High voltage and low output capacitance  $V_{\text{CEO}} = -200 \text{ V}$ , Cob = 5.0 pF typ
- Suitable for wide band video amplifier

#### **Outline**

TO-126 MOD

1. Emitter
2. Collector
3. Base



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#### **Absolute Maximum Ratings** ( $Ta = 25^{\circ}C$ )

Item	Symbol	Ratings	Unit
Collector to base voltage	V <sub>CBO</sub>	-200	V
Collector to emitter voltage	V <sub>CEO</sub>	-200	V
Emitter to base voltage	$V_{EBO}$	-5	V
Collector current	I <sub>c</sub>	-0.2	A
Collector peak current	I <sub>C(peak)</sub>	-0.5	A
Collector power dissipation	P <sub>c</sub>	1.25	W
	P <sub>c</sub> *1	10	
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

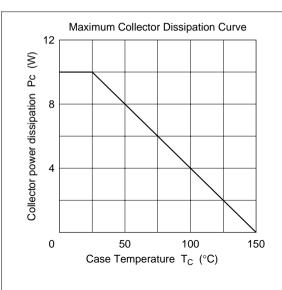
Note: 1. Value at  $T_c = 25$ °C.

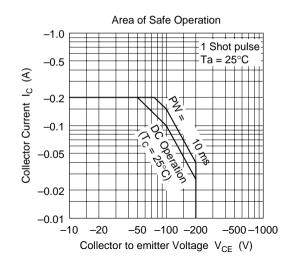
## **Electrical Characteristics** ( $Ta = 25^{\circ}C$ )

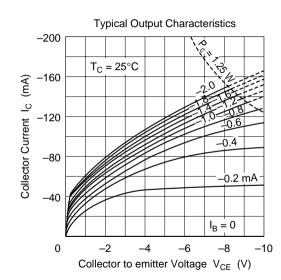
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-200	_	_	V	$I_{c} = -10 \ \mu A, \ I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-200	_	_	V	$I_{c} = -1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	<b>-</b> 5	_	_	V	$I_{E} = -10 \ \mu A, \ I_{C} = 0$
Collector cutoff current	I <sub>CBO</sub>	_	_	-10	μΑ	$V_{CB} = -160 \text{ V}, I_{E} = 0$
DC current transfer ratio	h <sub>FE</sub> *1	60	_	200		$V_{CE} = -5 \text{ V}, I_{C} = -10 \text{ mA}$
Base to emitter voltage	$V_{BE}$	_	_	-1.0	V	$V_{CE} = -5 \text{ V}, I_{C} = -30 \text{ mA}$
Collector to emitter saturation voltage	$V_{\text{CE}(\text{sat})}$	_	_	-1.0	V	$I_{\rm C} = -30 \text{ mA}, I_{\rm B} = -3 \text{ mA}$
Gain bandwidth product	f <sub>T</sub>	200	300	_	MHz	$V_{CE} = -20 \text{ V}, I_{C} = -30 \text{ mA}$
Collector output capacitance	Cob	_	5.0	_	pF	$V_{CB} = -30 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$

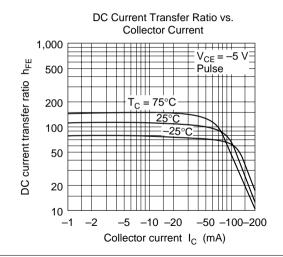
Note: 1. The 2SA1810 is grouped by h<sub>FE</sub> as follows.

В	С
60 to 120	100 to 200

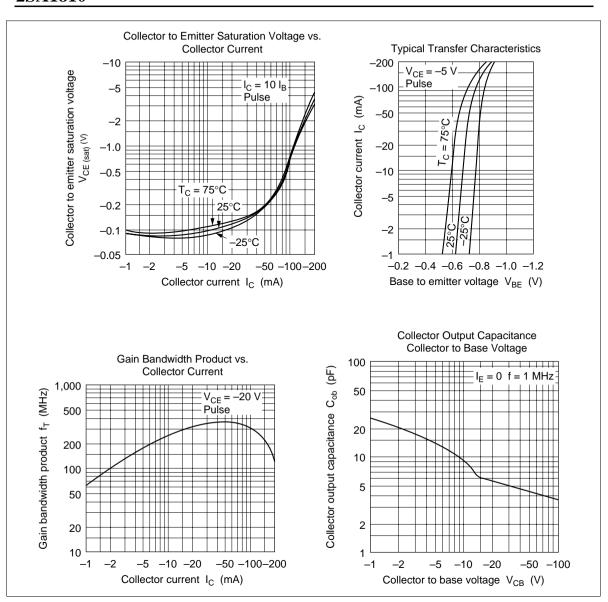




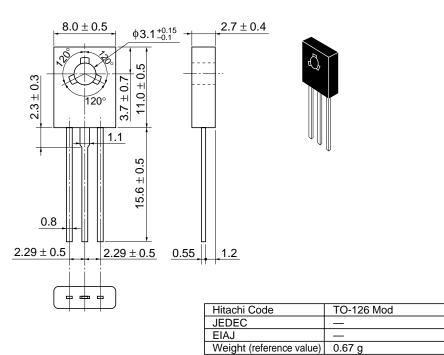




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Unit: mm



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